/ Descriptions

TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

/ Features

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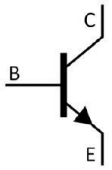
Low noise, high DC current gain, high breakdown voltage

/ Applications

Low noise audio amplifier applications.

/ Equivalent Circuit



/ Pinning



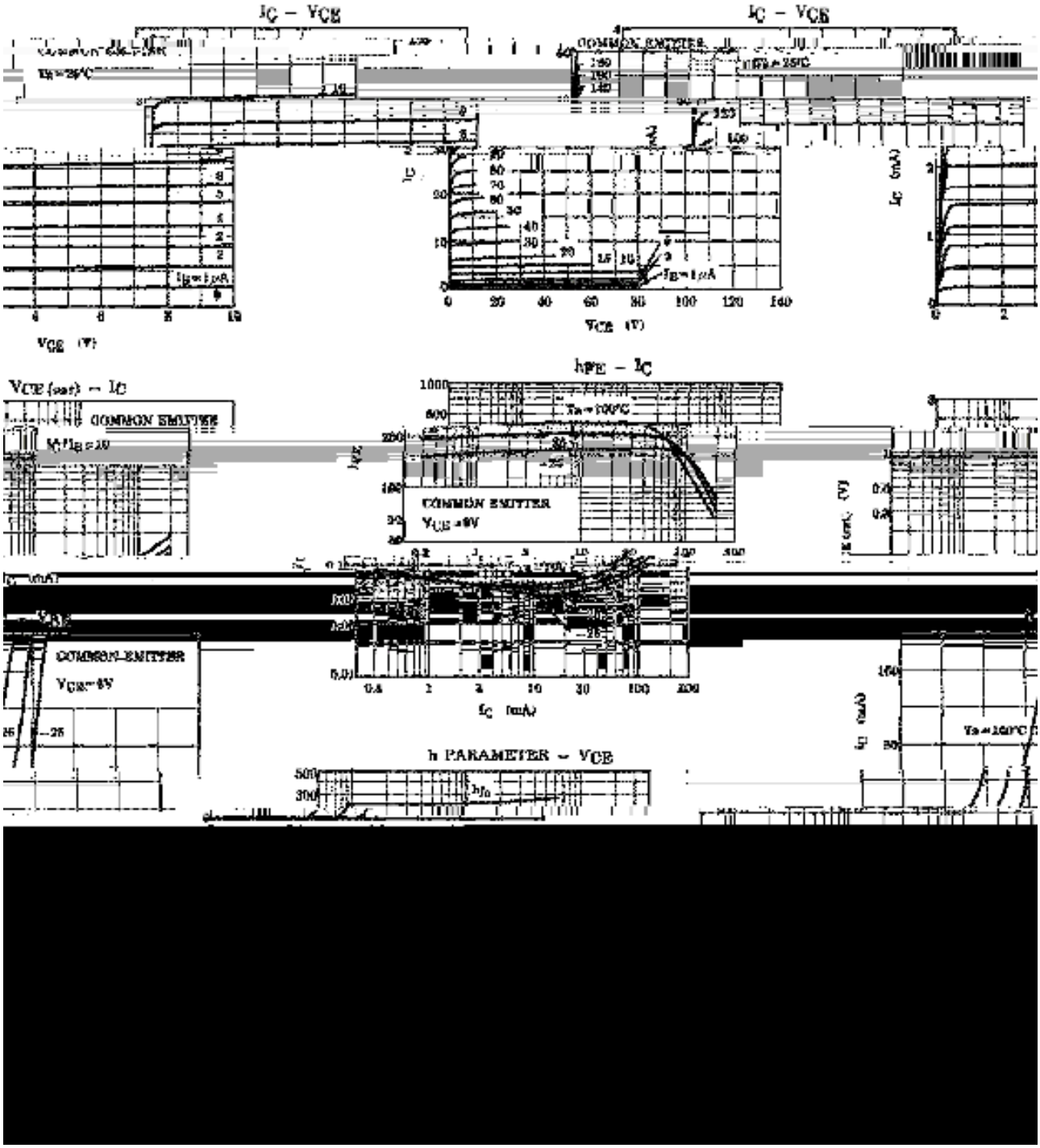
PIN1 Base PIN 2 Collector PIN 3 Emitter

/ hFE Classifications & Marking

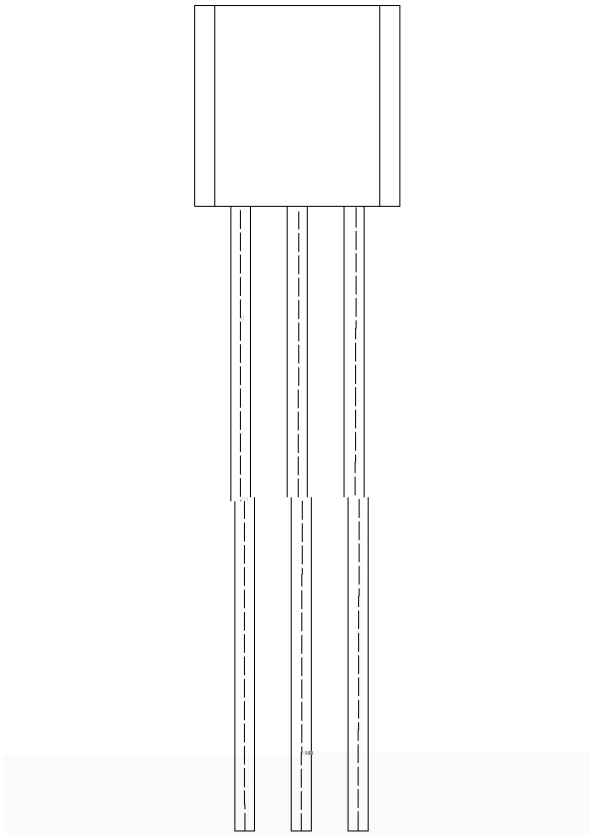
h_{FE} Classifications Symbol	GR	BL
h_{FE} Range	200~400	350~700

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	120	V
Collector to Emitter Voltage	V_{CEO}	120	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Emitter Current - Continuous	I_E	-100	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	152 591d560TJ/TT7 6 1 Tf8 TD10752	

/ Electrical Characteristic Curve



/ Marking Instructions



BR:

C2240

GR: h_{FE}

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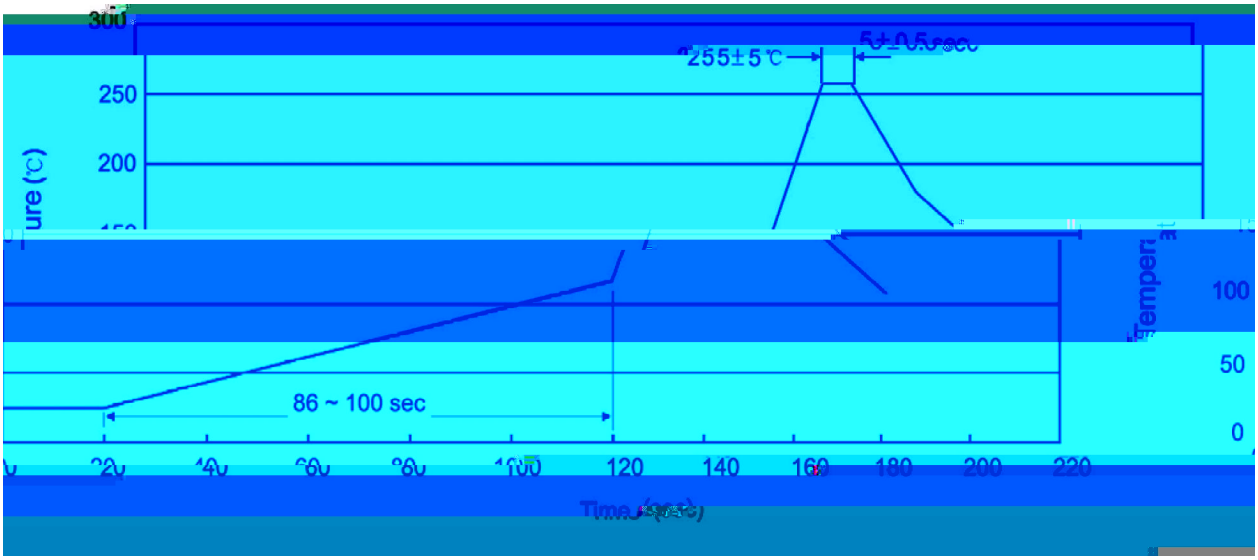
Note:

yewuction0037j0 -1.983 Tm557 TD0 TcGR:9 TD( )Tj/TT1TjE10.5533 0000.0005 74.2610in>1577.9600031514.9e00

( ) / Temperature Profile for Dip Soldering(Pb-Free)



					Note:
1		25 150		60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2		255±5		5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3			2 10	/sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	10,000	10	100,000	135×190	237×172×102	560×245×375

/ AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	Units/tape 只/纸带	Tape/Inner Box 纸带/盒	Rows/Inner Box 纸带层/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Inner Box 盒	Outer Box 箱
TO-92	3,000	1	120	10	30,000	328×230×42	小箱 480×346×235， 大箱 547×407×268

/ Notices